

## **GNSS Front-End Module**

#### **■ FEATURES**

- AEC-Q100 grade 2 qualified
- Low supply voltage 2.8V typ.
- Low current consumption 3.7mA typ.
- High gain 16.0dB typ.
- Low noise figure

1.50dB typ. @f=1575MHz

1.65dB typ. @f=1597 to 1606MHz

1.70dB typ. @f=1559 to 1591MHz

High out band rejection

55dBc typ. @f=704 to 915MHz, relative to 1575MHz 43dBc typ. @f=1710 to 1980MHz, relative to 1575MHz 51dBc typ. @f=2400 to 2500MHz, relative to 1575MHz

- Integrated pre-SAW filter and LNA
- Small package size

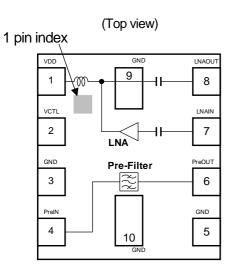
HFFP10-HH 1.5mmx1.1mm (typ.), t=0.5mm (max.)

• RoHS compliant and Halogen Free, MSL1

#### **■ APPLICATION**

- GNSS application for automotive
- •GNSS active antenna

#### **■ BLOCK DIAGRAM** (HFFP10-HH)



#### **■ GENERAL DESCRIPTION**

The NJG1159PHH-A is a front-end module (FEM) designed for GNSS including GPS, GLONASS, BeiDou, and Galileo applications. This FEM offers low noise figure, high linearity, and high out-band rejection characteristics brought by included high performance pre-SAW filter and low noise amplifier (LNA). The stand-by mode contributes to reduce current consumption.

Its wide operating temperature range from -40 to +105°C is suitable for automotive application.

This FEM is suitable for small size application by included one SAW filter, only two external components, and very small package HFFP10-HH that is 1.5x1.1mm.

#### **■ TRUTH TABLE**

"H"=V<sub>CTL(H),</sub> "L"=V<sub>CTL(L)</sub>

Vctl	Mode
Н	Active mode
L	Stand-by mode

#### **■ PIN CONFIGURATION**

PIN NO.	SYMBOL	DESCRIPTION
1	VDD	Supply voltage terminal
2	VCTL	Control voltage terminal
3	GND	Ground terminal
4	PrelN	RF input terminal to
4	PIEIN	Pre-SAW filter
5	GND	Ground terminal
6	PreOUT	RF output terminal from
	PIEOUI	Pre-SAW filter
7	LNAIN	RF input terminal to LNA
8	LNAOUT	RF output terminal from LNA
9	GND	Ground terminal
10	GND	Ground terminal

#### **■ PRODUCT NAME INFORMATION**

#### **■ ORDERING INFORMATION**

PART NUMBER	PACKAGE OUTLINE	RoHS	HALOGEN- FREE	TERMINAL FINISH	MARKING	WEIGHT (mg)	MOQ (pcs.)
NJG1159PHH-A	HFFP10-HH	Yes	Yes	Au	59A	4.6	3,000

#### ■ ABSOLUTE MAXIMUM RATINGS

 $T_a=+25$ °C.  $Z_s=Z=50\Omega$ 

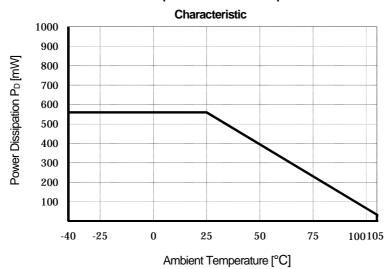
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PARAMETER	SYMBOL	RATINGS	UNIT
Supply voltage	$V_{DD}$	5.0	V
Control voltage	Vctl	5.0	V
Input power	P <sub>IN</sub> (inband) (1)	+10	dBm
	P <sub>IN</sub> (outband) (2)	+25	dBm
Power dissipation	P <sub>D</sub> <sup>(3)</sup>	560	mW
Operating temperature	Topr	-40 to +105	°C
Storage temperature	T <sub>stg</sub>	-40 to +110	°C

- (1): V<sub>DD</sub>=2.8V, f=1575, 1597 to 1606, 1559 to 1591MHz
- (2):  $V_{DD}$ =2.8V, f=50 to 1460, 1710 to 4000MHz
- (3): 4-layer FR4 PCB without through-hole (101.5x114.5mm),  $T_j$ =110°C

## ■ POWER DISSIPATION VS.AMBIENT TEMPERATURE

Please note small non-lead package generally has low thermal dissipation characteristic, attention is recommended in designing of thermal radiation.

#### **Power Dissipation - Ambient Temperature**



New Japan Radio Co., Ltd.

## ■ ELECTRICAL CHARACTERISTICS 1 (DC)

(General conditions:  $T_a = 25$ °C, with application circuit)

PARAMETER	SYMBOL	CONDITION	MIN.	TYP.	MAX.	UNIT
Supply Voltage	$V_{DD}$		1.5	2.8	3.3	V
Control Voltage (High)	V <sub>CTL(H)</sub>		1.5	1.8	3.3	V
Control Voltage (Low)	V <sub>CTL(L)</sub>		0	0	0.3	V
Supply Current 1	I <sub>DD1</sub>	RF OFF, V <sub>DD</sub> =2.8V, V <sub>CTL</sub> =1.8V	-	3.7	6.5	mA
Supply Current 2	I <sub>DD2</sub>	RF OFF, V <sub>DD</sub> =2.8V, V <sub>CTL</sub> =0V	-	0.1	5.0	μA
Control Current	lcτι	V <sub>Cπ</sub> =1.8V	-	5.0	15.0	μA

## ■ ELECTRICAL CHARACTERISTICS 2 (RF)

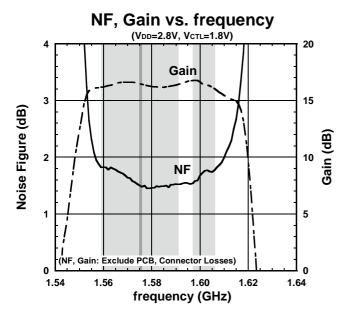
General conditions:  $V_{DD}$ =2.8V,  $V_{CTL}$ =1.8V,  $f_{RF}$ =1575MHz, 1597 to 1606MHz, 1559 to 1591MHz,  $T_a$ =+25°C,  $Z_s$ = $Z_i$ =50 $\Omega$ , with application circuit

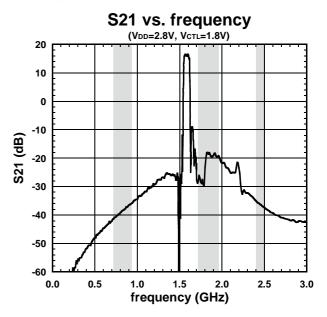
PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Small Signal Gain	GainGPS	f=1575MHz (GPS)	13.5	16.0	-	dB
(GPS)	Gailiges	Exclude PCB, Connector Losses (0.17dB)	13.3			
Small Signal Gain	GainGLN	f=1597 to 1606MHz (GLONASS)	13.0	16.5	-	dB
(GLONASS)	GailiGLIN	Exclude PCB, Connector Losses (0.17dB)	13.0			
Small Signal Gain	GainBG	f=1559 to 1591MHz (BeiDou, Galileo)	13.0	16.0	-	dB
(BeiDou, Galileo)	GairibG	Exclude PCB, Connector Losses (0.17dB)	13.0	10.0		
Noise Figure	NFGPS	f=1575MHz (GPS)Exclude PCB,		1.50	2.35	dB
(GPS)	INFGFS	Connector Losses (0.09dB)	-			
Noise Figure	NFGLN	f=1597 to 1606MHz (GLONASS)		1.65	2.70	dB
(GLONASS)	INFGLIN	Exclude PCB, Connector Losses (0.09dB)	-			
Noise Figure	NFBG	f=1559 to 1591MHz (BeiDou, Galileo)		1.70	2.80	dB
(BeiDou, Galileo)	NFBG	Exclude PCB, Connector Losses (0.09dB)	-			
Input Power at 1dB Gain	P-1dB(IN)	f=1575,	-15.0	-10.0		dBm
Compression Point	F-Tub(IIV)	1597 to 1606, 1559 to 1591MHz	-15.0	-10.0	-	UDITI
Low Band Rejection	BR_L	f=704 to 915MHz,	41	55	-	dBc
Low Band Rejection		relative to 1575MHz	41			
High Band Rejection	ᄝᄆᄔ	f=1710 to 1980MHz,	23	43		dBc
	BR_H	relative to 1575MHz	23	40	_	ubc
MI AN Pand Paination	BR_W	f=2400 to 2500MHz,	38	51	-	dBc
WLAN Band Rejection		relative to 1575MHz	30			

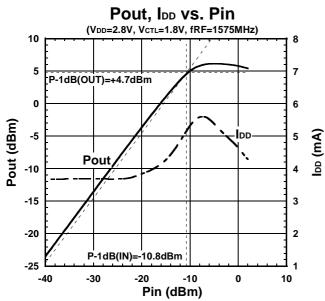


## **■ ELECTRICAL CHARACTERISTICS**

Conditions:  $V_{DD}$ =2.8V,  $V_{CTL}$ =1.8V, Ta=25°C,  $Z_s$ = $Z_l$ =50 $\Omega$ , with application circuit



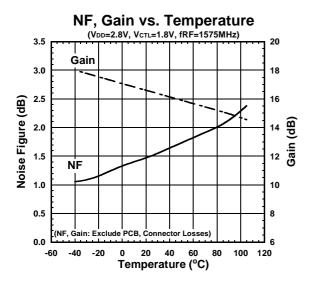


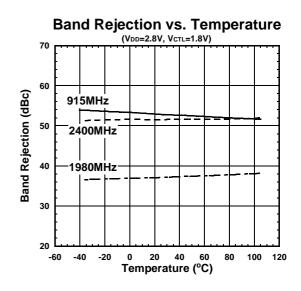


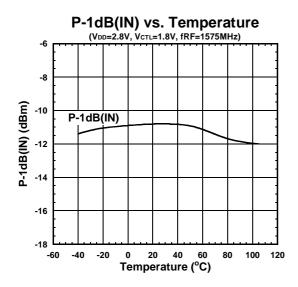


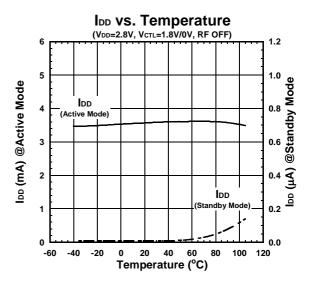
## **■ ELECTRICAL CHARACTERISTICS**

Conditions:  $V_{DD}$ =2.8V,  $V_{CTL}$ =1.8V,  $Z_s$ = $Z_l$ =50 $\Omega$ , with application circuit





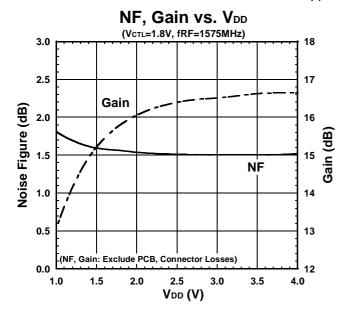


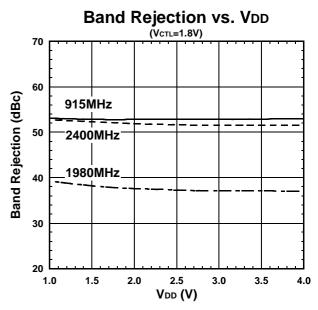


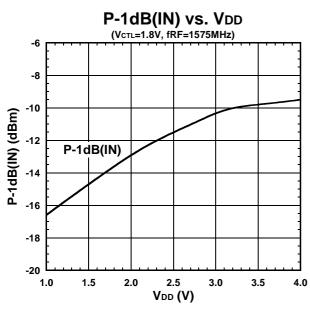


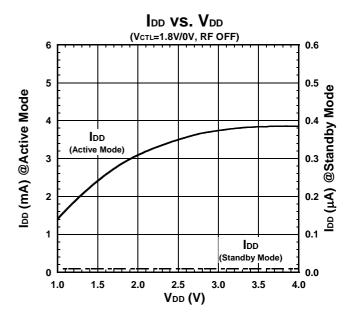
## **■ ELECTRICAL CHARACTERISTICS**

Conditions: V<sub>CTL</sub>=1.8V, Ta=25°C, Z<sub>s</sub>=Z<sub>i</sub>=50Ω, with application circuit



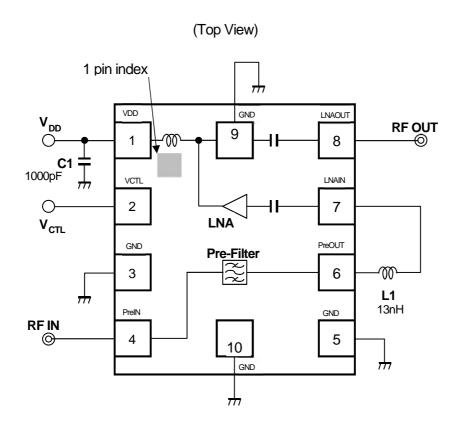








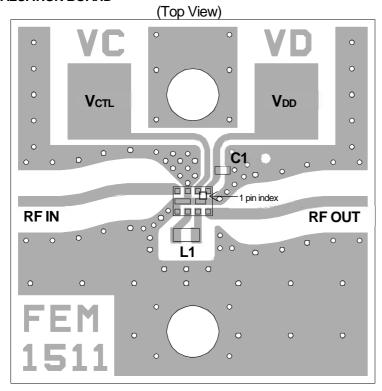
## **■ APPLICATION CIRCUIT**



## <PARTS LIST>

Part ID	Note	
11	LQW15AN_00 Series	
LI	(MURATA)	
C1	GRM03 Series	
CI	(MURATA)	

#### **■ EVALUATION BOARD**



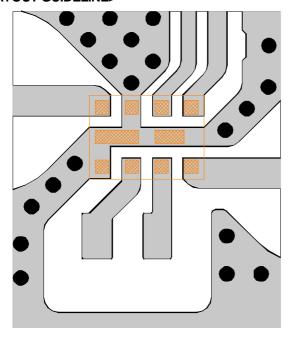
**PCB** 

Substrate: FR-4 Thickness: 0.2mm

Microstrip line width: 0.4mm ( $Z_0$ = $50\Omega$ )

Size: 14.0mm x 14.0mm

#### <PCB LAYOUT GUIDELINE>



PCB

XX PKG Terminal

PKG Outline

GND Via Hole

Diameter *ϕ*= 0.2mm

#### **PRECAUTIONS**

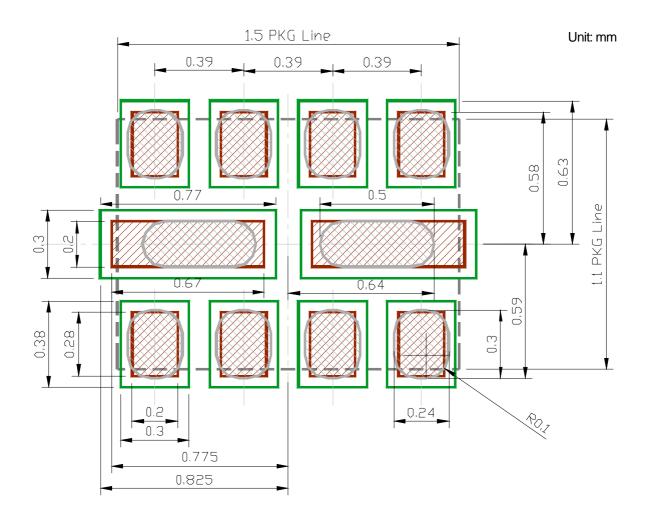
- Please layout ground pattern under this FEM in order not to couple with RFIN and RFOUT terminal.
- All external parts should be placed as close as possible to the FEM.
- For good RF performance, all GND terminals must be connected to PCB ground plane of substrate, and via-holes for GND should be placed near the FEM.

## ■ RECOMMENDED FOOTPRINT PATTERN (HFFP10-HH Package) <Reference>

PKG: 1.5mm x 1.1mm Pin pitch: 0.39mm : Land

: Mask (Open area) \*Metal mask thickness : 100µm

: Resist (Open area)



#### ■ NOISE FIGURE MEASUREMENT BLOCK DIAGRAM

#### **Measuring instruments**

NF Analyzer : Keysight N8973A Noise Source : Keysight 346A

#### Setting the NF analyzer

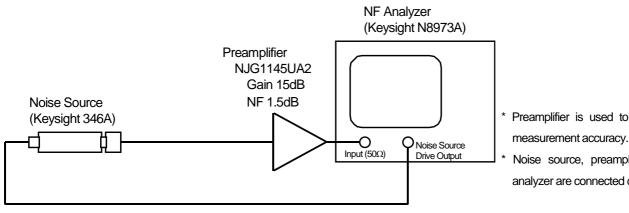
Measurement mode form

Device under test : Amplifier System downconverter : off

Mode setup form

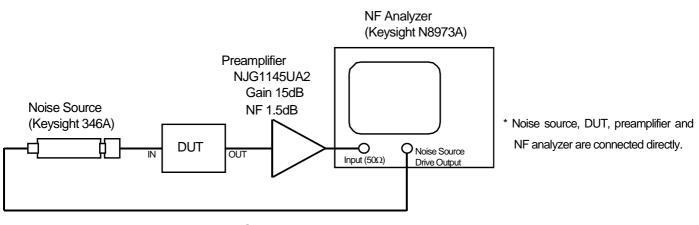
Sideband : LSB **Averages** : 16 Average mode : Point Bandwidth : 4MHz : off Loss comp

Tcold : setting the temperature of noise source (303.15K)



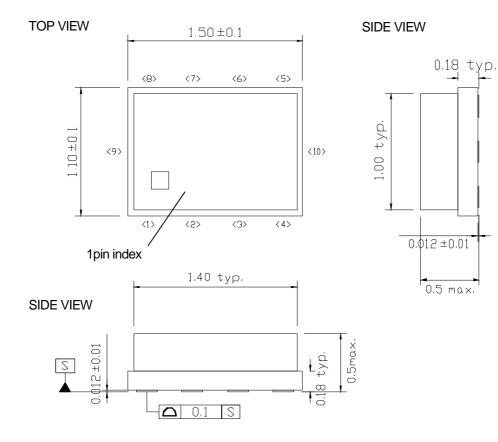
- Preamplifier is used to improve NF
- Noise source, preamplifier and NF analyzer are connected directly.

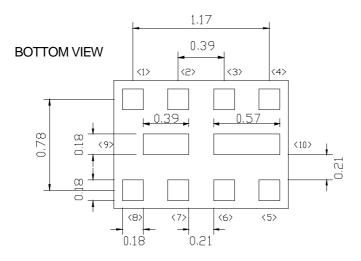
## **Calibration setup**



## **Measurement Setup**

## ■ PACKAGE OUTLINE (HFFP10-HH)





Electrode Dimensions clearance

: ±0.05mm

Unit : mm
Substrate : Ceramic
Terminal treat : Au

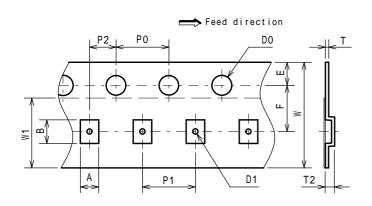
Lid : SnAg/Kovar/Ni

Weight (typ.) : 4.6mg

## ■ PACKING SPECIFICATION (HFFP10-HH)

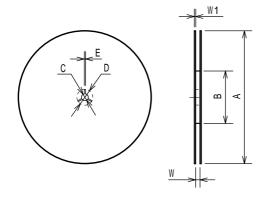
#### **TAPING DIMENSIONS**

Unit: mm



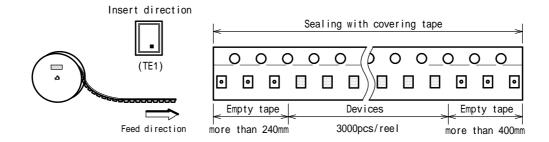
SYMBOL	DIMENSION	REMARKS
Α	$1.4 \pm 0.1$	BOTTOM DIMENSION
В	$1.8 \pm 0.1$	BOTTOM DIMENSION
D0	1.5 +0.1	
D1	$0.5 \pm 0.05$	
E	$1.75 \pm 0.1$	
F	$3.5 \pm 0.05$	
P0	$4.0 \pm 0.1$	
P1	$4.0 \pm 0.1$	
P2	$2.0 \pm 0.05$	
T	$0.25 \pm 0.05$	
T2	$0.7 \pm 0.1$	
W	$8.0 \pm 0.2$	
W1	$5.3 \pm 0.2$	THICKNESS100 µ m max

#### **REEL DIMENSIONS**

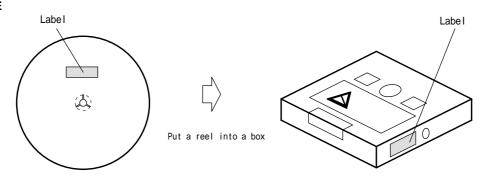


SYMBOL	DIMENSION
Α	180 -1.5
В	66 ± 0.5
С	13 ± 0.2
D	21 ± 0.8
Е	2±0.5
W	9 +1.0
W1	1.2

#### **TAPING STATE**



## **PACKING STATE**





## **■ REVISION HISTORY**

Date	Revision	Changes
15.Nov.2016	Ver.1.0	New Release Automotive spec
		Changed package suffix from H to A
19.Jul.2017	Ver.1.1	Updated ELECTRICAL CHARACTERISTICS 1 (DC)
19.Jul.2017	vei.i.i	Updated ELECTRICAL CHARACTERISTICS 2 (RF)
		Added packing specification
10 Oct 2019	Vor 1.0	Revised features
19.001.2016	19.Oct.2018 Ver.1.2	Revised caution
		Revised MARK INFORMATION
08.Nov.2018	Ver.1.3	Revised ORDERING INFORMATION
		Revised weight
		Revised features
		Added APPLICATION
		Revised PRODUCT NAME INFORMATION
08.Jan.2019	Ver.1.4	Revised ORDERING INFORMATION
		Revised ELECTRICAL CHARACTERISTICS 2 (RF)
		Added POWER DISSIPATION VS.AMBIENT TEMPERATURE
		Revised caution

#### [CAUTION]

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  catastrophic system failures
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  - · Equipment Used in the Deep Sea
  - · Power Generator Control Equipment (Nuclear, steam, hydraulic, etc.)
  - · Life Maintenance Medical Equipment
  - · Fire Alarms / Intruder Detectors
  - · Vehicle Control Equipment (Airplane, railroad, ship, etc.)
  - · Various Safety Devices



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- 8. Warning for handling Gallium and Arsenic (GaAs) Products (Applying to GaAs MMIC, Photo Reflector). These products use Gallium (Ga) and Arsenic (As) which are specified as poisonous chemicals by law. For the prevention of a hazard, do not burn, destroy, or process chemically to make them as gas or power. When the product is disposed of, please follow the related regulation and do not mix this with general industrial waste or household waste.
- 9. This product may be damaged with electric static discharge (ESD) or spike voltage. Please handle with care to avoid these damages.
- 10. This product is hollow seal package type, and it is with the structure susceptible to stress from the outside. Therefore, note the following in relation to the contents, after conducting an evaluation, please use.

After mounting this product, to implement the potting and transfer molding, please the confirmation of resistance to temperature changes and shrinkage stress involved in the molding.

When mounted on the product, collet diameter please use more than 1mmp. In addition, the value of static load is recommended mounting less than 5N.

For dynamic load at the time of mounting, please use it after confirming in consideration of the contact area / speed / load.

11. The product specifications and descriptions listed in this datasheet are subject to change at any time, without notice.

